Growth and scattering mechanisms of metamorphic $In_{0.81}Ga_{0.19}As$ quantum wells

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Supplementary Figures:

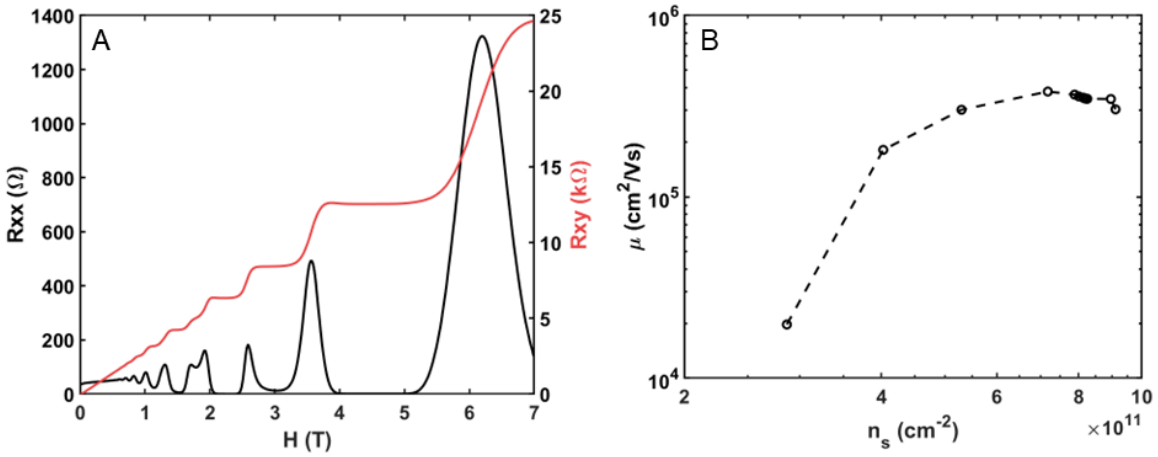

Figure 1: a) Low temperature (2 K) magnetotransport of an $In_{0.81}Ga_{0.19}As$ quantum well. b) Electron mobility as a function of carrier density of a gated $In_{0.81}Ga_{0.19}As$ quantum well.